



# DCR3480B52

# **Phase Control Thyristor**

Replaces DS5822-4 DS5822-5 June 2022 (LN41783)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		Tvj = -40°C to 125°C,
DCR3480B52*	5200	IDRM = IRRM = 300mA,
DCR3480B50	5000	VDRM, VRRM tp = 10ms
DCR3480B48	4800	VDSM & VRSM =
DCR3480B46	4600	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR3480B52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

$V_{DRM}$	5200V
I <sub>T(AV)</sub>	3440A
Ітѕм	49000A
dV/dt*	1500V/µs
dl/dt	400A/μs

<sup>\*</sup> Higher dV/dt selections are available on request

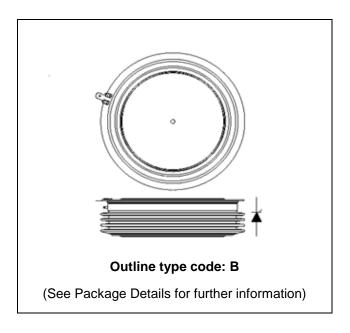


Fig. 1 Package outline

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<sup>\*5000</sup>V @ -40°C, 5200V @ 0°C



## **CURRENT RATINGS**

## T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
İT(AV)	Mean on-state current	Half wave resistive load	3440	А
IT(RMS)	RMS value	-	5400	Α
lτ	Continuous (direct) on-state current	-	4880	А

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	49.0	kA
l²t	I2t for fusing	V <sub>R</sub> = 0	12.0	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	7.0	°C/kW
Rth(j-c)	Rth(j-c) Thermal resistance - junction to case	Single side cooled	Anode DC	-	11.5	°C/kW
			Cathode DC	-	18.1	°C/kW
D	Clamp	Clamping force 76kN (with mounting compound)	Double side	-	1.4	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink		Single side	-	2.8	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			68	84	kN

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# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	300	mA
<b>V</b> тм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.50	1.75	٧
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub> Gate source 30V, 10Ω	Repetitive 50Hz	-	200	A/µs
ui/ut	ivate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	400	A/µs
V	Threshold voltage - Low level	500A to 2800A at Tcase = 125°C		-	0.87	٧
<b>V</b> т(то)	Threshold voltage - High level	2800A to 7000A at Tcase = 125°C		-	1.09	٧
_	On-state slope resistance - low level	500A to 2800A at Tcase = 125°C		-	0.25	mΩ
ľΤ	On-state slope resistance - High level	2800A to 7000A at Tcase = 125°C		-	0.17	mΩ
tgd	Delay time	$V_D = 67\%$ $V_{DRM}$ , gate source 30V, $10\Omega$ $t_T = 0.5 \mu s$ , $T_j = 25 ^{\circ} C$		-	3	μs
tq	Turn-off time	T <sub>j</sub> = 125°C, V <sub>R</sub> = 200V, dl/dt = 1A/μs, dV <sub>DR</sub> /dt = 20V/μs linear		400	750	μs
Qs	Stored charge	I <sub>T</sub> = 2000A, T <sub>j</sub> = 125°C, dI/dt = 1A/μs V <sub>R</sub> (peak) ~ 3100V, V <sub>RM</sub> ~2100V		2700	6330	μC
IRR	Reverse recovery current			45	69	А
lι	Latching current	Tj = 25°C, VD = 5V		-	3	Α
Ін	Holding current	Tj = 25°C, Rg-к = ∞, Iтм = 500A, Iт = 5A		-	300	mA

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### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
<b>V</b> GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	٧
<b>V</b> GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
lgp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

### **CURVES**

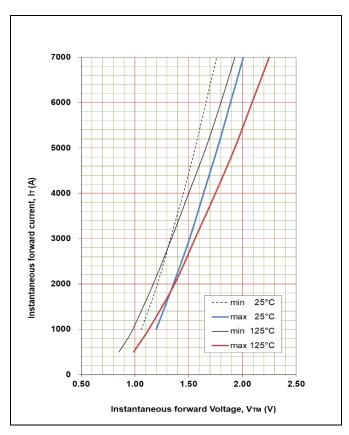


Fig. 2 Maximum & minimum on-state characteristics

## **VTM EQUATION**

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.706988

B = -0.002428

C = 0.000090

D = 0.011102

These values are valid for  $T_j$  = 125°C for  $I_T$  500A to 7000A

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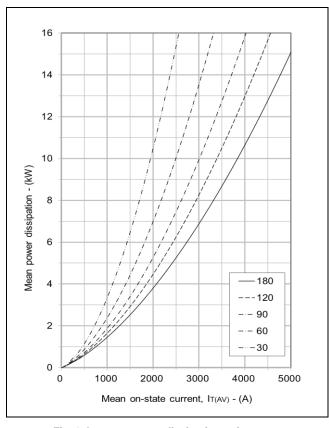


Fig. 3 On-state power dissipation - sine wave

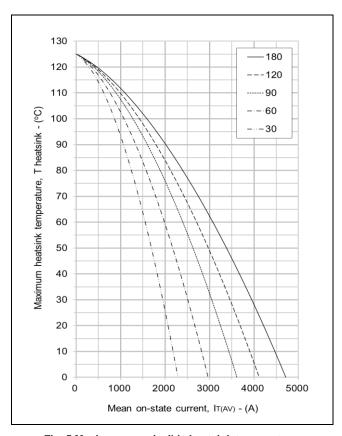


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

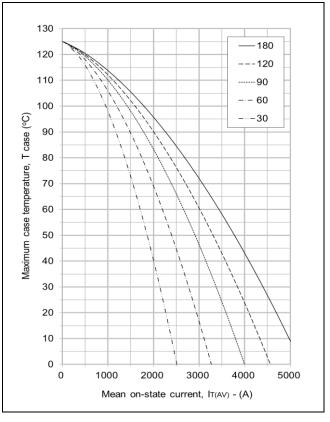


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

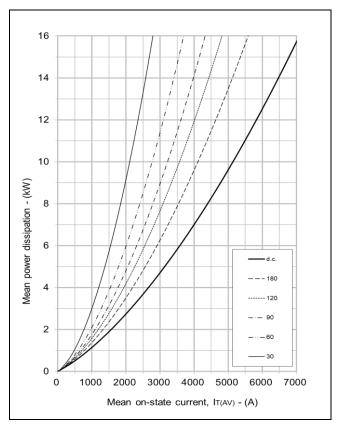


Fig. 6 On-state power dissipation - rectangular wave

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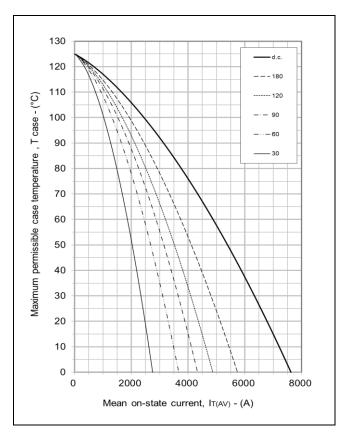
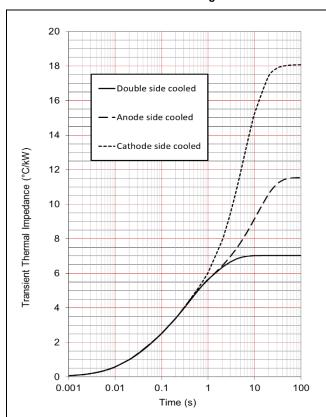


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



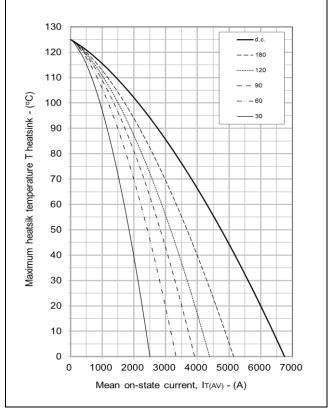


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.502	1.333	2.956	2.234
cooled	Ti(s)	0.014	0.055	0.331	1.691
Anode side cooled	Ri(°C/kW)	1.304	3.138	1.186	5.914
	Ti(s)	0.025	0.241	1.081	11.002
Cathode side cooled	Ri(°C/kW)	1.262	2.622	13.360	0.830
	Ti(s)	0.025	0.201	5.785	16.765

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

Tables show the increments of thermal resistance R  $_{\text{th}(j-c)}$  when the device operates at conduction angles other than d.c.

	Double side cooling				
	$\Delta Z_{th}$ (	(z)			
θ°	sine.	rect.			
180	0.70	0.48			
120	0.80	0.68			
90	0.90	0.78			
60	1.00	0.89			
30	1.07	1.01			
15	1 10	1.07			

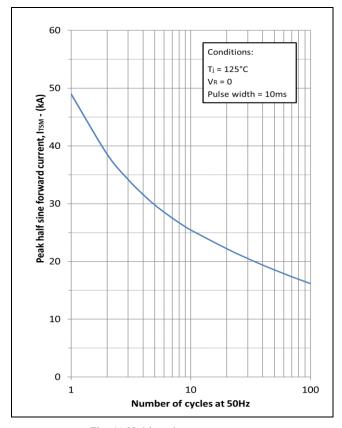
l		Alloue Slue	Cooling
		$\Delta Z_t$	<sub>h</sub> (z)
	θ°	sine.	rect.
	180	0.67	0.47
	120	0.77	0.66
	90	0.87	0.75
	60	0.95	0.86
	30	1.02	0.96
	15	1.05	1.02

Ca	thode Sided Cooling		
	$\Delta Z_t$	<sub>h</sub> (z)	
θ°	sine.	rect.	
180	0.67	0.47	
120	0.77	0.66	
90	0.87	0.76	
60	0.95	0.86	
30	1.02	0.96	
15	1.05	1.02	

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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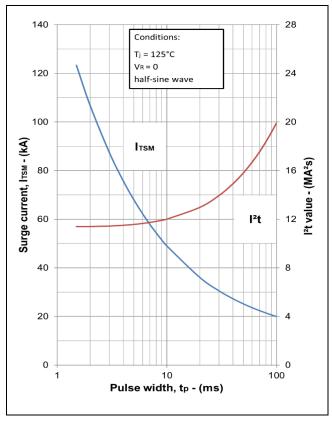


Fig. 10 Multi-cycle surge current

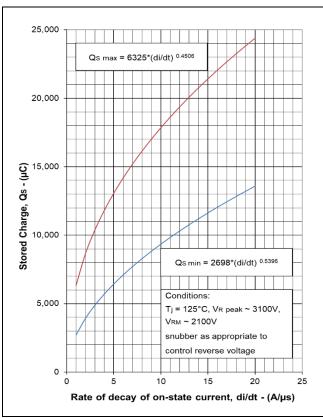


Fig. 12 Reverse recovery charge

Fig. 11 Single-cycle surge current

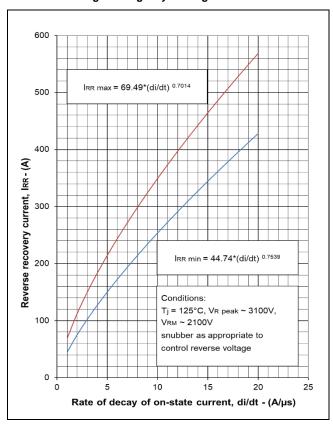


Fig. 13 Reverse recovery current

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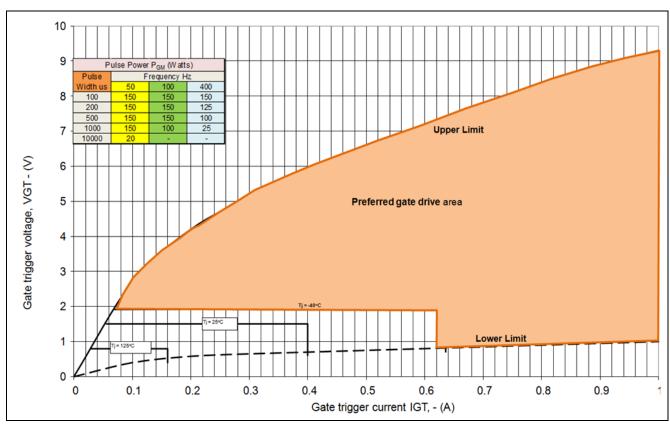


Fig. 14 Gate characteristics

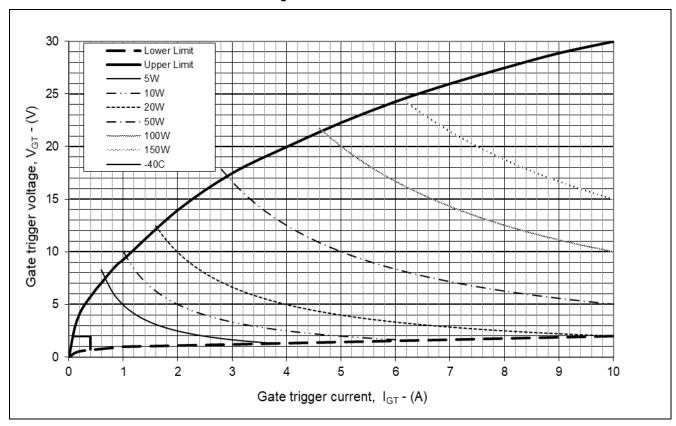


Fig. 15 Gate characteristics

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### **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

### DO NOT SCALE

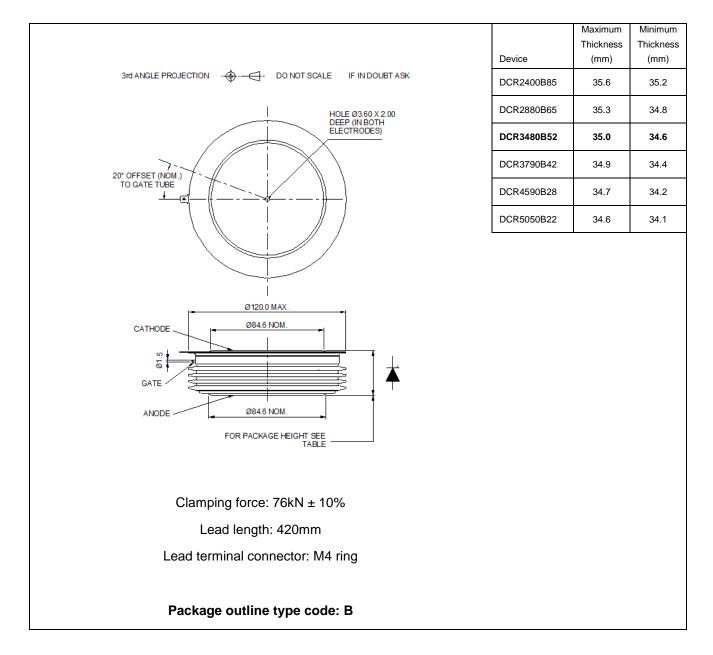


Fig. 16 Package outline

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